A new type of cyclotron resonance from charge-impurity scattering in the bulk-insulating Bi$_2$Se$_3$ thin films

Xingyue Han, Maryam Salehi, Seongshik Oh, and Liang Wu

$^1$Department of Physics and Astronomy, University of Pennsylvania, Philadelphia, PA 19104 USA.
$^2$Department of Material Science and Engineering, Rutgers the State University of New Jersey, Piscataway, NJ 08854 USA.
$^3$Department of Physics and Astronomy, Rutgers the State University of New Jersey, Piscataway, NJ 08854 USA.

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We have utilized time-domain terahertz spectroscopy to investigate the low frequency Drude response of bulk-insulating topological insulator Bi$_2$Se$_3$ films grown on buffer layers under a magnetic field up to 7 Tesla. With both field and frequency dependence, such experiments measure the mobility and carrier density of multiple surface conduction channels simultaneously. We observe sharp cyclotron resonances (CRs), and it is consistent with conduction from two different topological surface states (TSSs) on top and bottom of the films. The CR sharpens at high fields, an effect that we attribute to an electron-impurity scattering. This work shows that cyclotron resonance is a powerful tool to study many-body interactions in topological materials.

Ordered states of matter are usually characterized by Landau’s spontaneous symmetry breaking theory. For example, ferromagnets break continuous rotation symmetry and superconductors break gauge symmetry. Three-dimensional topological insulators (TIs) are newly discovered states of matter with robust metallic surface states protected by the topological properties of their bulk wavefunctions $^3$ $^2$. In the ideal case, they have an insulating bulk and only conduct via topologically protected massless Dirac topological surface states (TSSs). Progress in this field were hampered by the fact that most of the TIs were slightly doped and had a conducting bulk. Tuning the chemical potential towards the Dirac point and enhancing mobility was shown to be very successful in probing many-body interactions with plasmons and phonons in graphene $^4$ $^3$ and similar advancements are expected in TIs, but have only studied in bulk-insulating Cu doped Bi$_2$Se$_3$ with dominating electron-phonon coupling $^4$.

The band structure of Bi$_2$Se$_3$ is one of the simplest of the 3D TIs with only a single Dirac cone on the surface. Unfortunately, native grown Bi$_2$Se$_3$ is known to have a conducting bulk due to defects from the growth. Suppression of the bulk carrier density has been achieved by chemical doping methods $^5$ $^6$. Nevertheless, these samples still have significant densities of bulk carriers or impurity states that are pinned near the chemical potential. Recently it was found that Bi$_2$Se$_3$ grown on buffer-layers suppresses the bulk carriers and allows a true insulating state to be realized $^7$ $^8$. Here we investigate these bulk insulating thin films and their decoupled TSSs via time-domain terahertz spectroscopy with a magnetic field up to 7 tesla.

Cyclotron resonance (CR) experiments using THz spectroscopy are a powerful tool to study Dirac fermions and probe many-body interactions $^9$ $^10$. CR is also one of the most accurate measures of effective mass $^11$. In previous work, a large Kerr rotation in bulk-conducting Bi$_2$Se$_3$ films was reported, but no obvious resonance was observed $^12$. Cyclotron resonance has been reported in In$_2$Se$_3$ capped films $^13$, but current understanding is that significant Indium diffusion from In$_2$Se$_3$ to Bi$_2$Se$_3$ $^14$ destroys the simple non-TI/TI boundary at the interface, as a topological phase transition occurs at low Indium concentrations (∼ 6%) $^15$. CR was also observed in bulk-insulating Cu doped Bi$_2$Se$_3$ films, and electron-phonon coupling was revealed perviously $^4$.

Here we report time-domain THz spectroscopy on bulk insulating Bi$_2$Se$_3$ grown on (Bi$_1$-In$_1$)$_2$Se$_3$ buffer layer (BIS-BL) $^7$. Fig.1(a)(b) shows real and imaginary conductance for 32QL and 16QL Bi$_2$Se$_3$ grown on BIS-BL at 5 K. Compared with normal Bi$_2$Se$_3$ directly on sapphire or Si, the spectral weight is reduced $^12$. The spectral weight is even lower than reported bulk-insulating Cu$_{0.02}$Bi$_2$Se$_3$ $^4$.

In principal the spectra can be fit by two oscillators model with Drude terms describing free electron-like motions from top and bottom surfaces separately, a Drude-Lorentz term modeling the phonon and a lattice polarizability $\epsilon_m$ term that originates from absorptions above the measured spectral range.

$$G(\omega) = \epsilon_0 d \left( \sum_{i=1}^{2} \frac{\omega^2 p_D G_{iD}}{i \omega - \Gamma_{iD}} - \frac{i \omega^2 p_{DL}}{\omega^2 - \Gamma_{DL} - i \omega \Gamma_{DL}} - i (\epsilon_m - 1) \omega \right)$$

Here $\Gamma$’s are scattering rates, $\omega_p$’s are plasma frequencies, and $d$ is the film thickness. The total spectral weight ($\omega_{pD}^2 d$) is proportional to the integrated area of each feature in the real part of the conductance $G_{D1}$. It gives the ratio of carrier density to an effective transport mass.

$$\frac{2}{\pi \epsilon_0} \int G_{D1} d\omega = \sum_{i=1}^{2} \omega^2_{pD} d = \sum_{i=1}^{2} \frac{n_{2D} e^2}{m_i^* \epsilon_0}$$

Here $m^*$ is defined as $\hbar k_F/v_F$ for “massless Dirac fermions”. Considering the TSS dispersion up to quadratic corrections $E = Ak_F + Bk_F^2$, the spectral weight can be expressed in terms of $k_F$, where A and B are parameters obtained from ARPES $^4$. For one surface state, the relation between spectral weight and $k_F$ is as following. Note that the right side of following expression is half of the value in the Bi$_2$Se$_3$ when we assume two nominally same TSSs were observed in Bi$_2$Se$_3$. 

$\omega_{pD}^2 d = \frac{\pi \epsilon_0}{2} \int G_{D1} d\omega = \sum_{i=1}^{2} \omega^2_{pD} d = \sum_{i=1}^{2} \frac{n_{2D} e^2}{m_i^* \epsilon_0}$
Bi$_2$Se$_3$ on BIS-BL 5K

32QL data
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32QL 1 Drude fit
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32QL 2 Drude fit
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16QL data

(a) Real conductance

(b) Imaginary conductance

FIG. 1: (Color online) (a) Real and (b) Imaginary conductance of 32QL and 16QL Bi$_2$Se$_3$ grown on BIS-BL at 5K.

$\omega_{pD}^2 = \frac{k_F(A + 2Bk_F)e^2}{4\pi\hbar^2\epsilon_0}$

At first, a single channel conduction originated in two nominally identical TSSs is also assumed here. From the spectral weight analysis, having determined $k_F$, we can then calculate both $n_{2D}$ (proportional to $k_F^2$) and $m^*$. From these Drude-Lorentz fits, we find a total sheet carrier density $n_{2D} \sim 4.8 \pm 0.12 \times 10^{12}/\text{cm}^2$, $m^* \sim 0.135 \pm 0.005 m_e$ and $E_F \sim 140 \pm 10 \text{ meV}$ according to Eq. (3) in 32QL sample. 16QL sample has lower spectral weight than 32QL sample. The same analysis gives a total sheet carrier density $n_{2D} \sim 3.8 \times 10^{12}/\text{cm}^2$, $m^* \sim 0.12 \pm 0.005 m_e$, and $E_F \sim 120 \pm 8 \text{ meV}$. The estimation of the chemical potential is consistent with an insulating bulk.[17]

We performed Faraday rotation measurements on these samples to measure the cyclotron resonance mass and spectral weight. Data are shown in Fig. 2(a)(b)(c)(d). Similar to Cu$_{0.02}$Bi$_2$Se$_3$, cyclotron resonances are observed in both 32QL and 16QL samples. We model the conductance in a magnetic field by the following expression and assume two equally contribution from top and bottom surface states:

$$G_s = -i\epsilon_0\omega d \left( \sum_{-1}^{2} \frac{\omega_{pD}^2}{\omega^2 - i\Gamma_{DL} + \omega_0\omega} + \frac{\omega_{pD}^2}{\omega_{pD}^2 - \omega^2 - i\omega\Gamma_{DL}} + (\epsilon_0 - 1) \right)$$

Here the $\pm$ sign signifies the response to right/left-hand circularly polarized light, respectively. $\omega_0$ is the CR frequency. The Faraday rotation can be expressed as $\tan(\theta_F) = -i(\Delta_+ - \Delta_-)/(\Delta_+ + \Delta_-)$. Here we let $\omega_0$ and $\Gamma_D$ vary with field. We find that the fit result is not as good as shown in Fig. 3(a). Let us further address the 1 Drude model analysis. As we can see in Fig 3(a), the fit quality of 1 Drude term is not as good as Cu$_{0.02}$Bi$_2$Se$_3$ case. Bi$_2$Se$_3$ is grown (Bi$_{1-x}$In$_x$)$_2$Se$_3$ and $\leq 0.2\%$ In is diffused into the bottom Bi$_2$Se$_3$ few layers. Even though 0.2% is far below the topological phase transition threshold[15], it is natural to treat top surface states (tSS) and bottom surface states (bSS) differently. We remove the equal contribution from both surface states and treat them separately as equation 4. The fit quality improve significantly as shown in Fig 3(a). We can also see two Drude terms fit zero-field conductance better in Fig. 3(b). Then we can extract carrier density of each surface state by the relation $\omega_{pD}^2 = \frac{n_{SS}e^2}{m_{SS}^*}$. The parameters for 2 Drude fits are showed in Table 1. Indium causes more scattering and therefore the channel with larger scattering rate is identified as bottom surface state.

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\begin{array}{|c|c|c|c|}
\hline
& \text{iSS 32QL} & \text{bSS 32QL} & \text{iSS 16QL} & \text{bSS 16QL} \\
\hline
B_{2D} (10^{12}/\text{cm}^2) & 2.2 & 2.7 & 1.3 & 2.0 \\
\hline
m^* (m_e) & 0.13 & 0.14 & 0.11 & 0.12 \\
\hline
\Gamma (7T) (\text{THz}) & 0.24 & 0.55 & 0.29 & 0.43 \\
\hline
\mu(7T) (\text{cm}^2/\text{Vs}) & 8980 & 3640 & 8780 & 5420 \\
\hline
\end{array}
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TABLE I: Fit parameters for two-Drude fit

Now let us address the decreasing scattering rate VS field as shown in Fig. 3(c-d). Short-range charge impurity scattering rate leads to $\sqrt{B}$ increasing scattering rate, as predicted and observed in graphene[16,18]. Electron-phonon scattering rate causes broadening of cyclotron resonance and saturation of scattering rate above phonon energy[4]. Long-range charge impurity scattering rate leads to decreasing scattering rate VS field[19]. It was not the dominant mechanism in graphene and therefore was never observed. Similar trend were reported in InSe quantum well and was interpreted as scattering over Gaussian potential larger or equal to the cyclotron orbit[20]. The saturation of scattering rate above 4T in Fig. 3(c-d) is due to electron-phonon scattering as cyclotron frequency reaches ~0.7 THz at 4 T in both samples which corresponds to either Kohn anomaly of surface $\beta$ phonon or highest acoustic phonon frequency[4]. In the two-Drude fit, one channel has stronger field dependence and is identified as bottom surface state. The reason is charge impurities most likely are created on the bottom surface state due to charge inhomogeneity. Top surface state has less effect due to screening.
This kind of long-range charge impurity scattering was further corroborated by the fact no Shubnikov de-Has (SdH) oscillation was observed on these sample while CR is very robust. SdH is limited by quantum life-time which is sensitive to both small-angle and large-angle scattering while CR is sensitive to transport life-time which is limited by back scattering. The low quantum life-time in these samples indicates significant small-angle scattering rate coming from long-range coulomb potential. Similar trend was observed in 2DEG system and theoretically investigated in literature.

To conclude, we observe sharp cyclotron resonance in bulk-insulating Bi$_2$Se$_3$ thin films. The field dependence reveals a decreasing of the scattering rate with increasing magnetic fields. We attribute the origin to impurity scattering due to the buffer layer. This work shows that cyclotron resonance is a powerful tool to study many-body interactions in topological materials.

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* Electronic address: liangwu@sas.upenn.edu

FIG. 3: (Color online) (a) A representative fit quality for 1 Drude fit (dashed line) and 2 Drude fit (solid line) and a calculation by using zero-field scattering rate (0TSC) of 32QL sample. (b) Cyclotron frequency VS field from 1 Drude fit. Solid line is linear fit. Drude scattering rate VS field from (c) 1 Drude fit (d) 2 Drude fit